

## SN74LVC244A Octal Buffer or Driver With 3-State Outputs

### 1 Features

- Operates from 1.65V to 3.6V
- Inputs accept voltages to 5.5V
- Specified from –40°C to +85°C and –40°C to +125°C
- Maximum t<sub>pd</sub> of 5.9ns at 3.3V
- Typical V<sub>OLP</sub> (output ground bounce) < 0.8V at V<sub>CC</sub> = 3.3V, T<sub>A</sub> =  $25^{\circ}C$
- Typical V<sub>OHV</sub> (output V<sub>OH</sub> undershoot)
  > 2V at V<sub>CC</sub> = 3.3V, T<sub>A</sub> = 25°C
- Supports mixed-mode signal operation on all ports (5V input or output voltage with 3.3V V<sub>CC</sub>)
- I<sub>off</sub> supports live insertion, partial-power-down mode, and back-drive protection
- Can be used as a down translator to translate inputs from a maximum of 5.5V down to the V<sub>CC</sub> level
- Available in ultra small logic QFN package (0.5mm maximum height)
- Latch-up performance exceeds 250mA per JESD 17

## 2 Applications

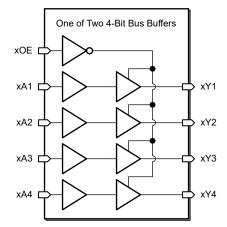
- Servers
- LED displays
- Network switches
- Telecom infrastructure
- Motor drivers
- I/O expanders

### **3 Description**

These octal bus buffers are designed for 1.65V to 3.6V V<sub>CC</sub> operation. The SN74LVC244A devices are designed for asynchronous communication between data buses.

Package Information										
PART NUMBER	PACKAGE <sup>(1)</sup>	PACKAGE SIZE <sup>(2)</sup>	BODY SIZE <sup>(3)</sup>							
	RKS (VQFN, 20) <sup>(4)</sup>	4.50mm × 2.50mm	4.50mm × 2.50mm							
	N (PDIP, 20)	24.33mm × 9.4mm	24.33mm × 6.35mm							
	NS (SOP, 20)	12.60mm × 7.8mm	12.60mm × 5.30mm							
	DB (SSOP, 20)	7.2mm × 7.8mm	7.2mm × 5.30mm							
SN74LVC244A	DGV (TVSOP, 20)	5.00mm × 6.4mm	5.00mm × 4.4mm							
SINTALV CZ44A	DW (SOIC, 20)	12.80mm × 10.3mm	12.80mm × 7.50mm							
	RGY (VQFN, 20)	4.50mm × 3.50mm	4.50mm × 3.50mm							
	ZQN (BGA, 20)	4.00mm × 3.00mm	4.00mm × 3.00mm							
	PW (TSSOP, 20)	6.50mm × 6.4mm	6.50mm × 4.40mm							
	RWP (X1QFN, 20)	3.30mm × 2.50mm	3.30mm × 2.50mm							

- (1) For more information, see Mechanical, Packaging, and Orderable Information.
- (2) The package size (length × width) is a nominal value and includes pins, where applicable.
- (3) The body size (length × width) is a nominal value and does not include pins.
- (4) Product Preview



Logic Diagram (Positive Logic)



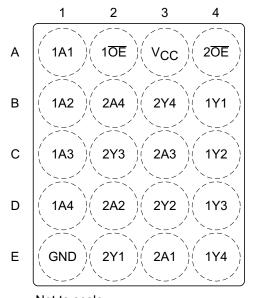
## **Table of Contents**

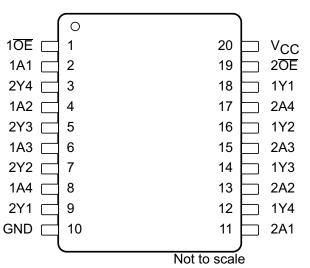
1 Features	1
2 Applications	1
3 Description	
4 Pin Configuration and Functions	
5 Specifications	5
5.1 Absolute Maximum Ratings	5
5.2 ESD Ratings	
5.3 Recommended Operating Conditions	
5.4 Thermal Information	6
5.5 Electrical Characteristics	7
5.6 Switching Characteristics	8
5.7 Operating Characteristics	8
5.8 Typical Characteristics	9
6 Parameter Measurement Information	10
7 Detailed Description	11
7.1 Overview	
7.2 Functional Block Diagram	11

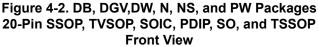
7.3 Feature Description	11
7.4 Device Functional Modes	
8 Application and Implementation	13
8.1 Application Information	
8.2 Typical Application	
8.3 Power Supply Recommendations	14
8.4 Layout	. 14
9 Device and Documentation Support	
9.1 Documentation Support	16
9.2 Receiving Notification of Documentation Updates	
9.3 Support Resources	16
9.4 Trademarks	16
9.5 Electrostatic Discharge Caution	16
9.6 Glossary	
10 Revision History	. 16
11 Mechanical, Packaging, and Orderable	
Information	. 17



### **4 Pin Configuration and Functions**







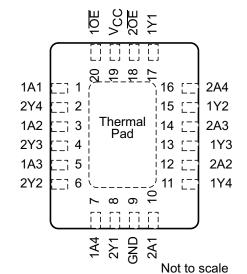
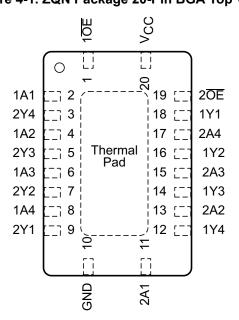


Figure 4-4. RWP Package 20-Pin X1QFN Top View

Not to scale Figure 4-1. ZQN Package 20-Pin BGA Top View



Not to scale Figure 4-3. RGY and RKS Packages 20-Pin VQFN Top View



			-	Table 4-1.	Pin Functions
		PIN			
NAME	DB, DGV, DW, N, NS, PW, RGY and RKS	ZQN	RWP	ТҮРЕ	DESCRIPTION
1A1	2	A1	1	I	Port 1 A1 input
1A2	4	B1	3	I	Port 1 A2 input
1A3	6	C1	5	I	Port 1 A3 input
1A4	8	D1	7	I	Port 1 A4 input
1 OE	1	A2	20	I	Output enable
1Y1	18	B4	17	0	Port 1 Y1 output
1Y2	16	C4	15	0	Port 1 Y2 output
1Y3	14	D4	13	0	Port 1 Y3 output
1Y4	12	E4	11	0	Port 1 Y4 output
2A1	11	E3	10	I	Port 2 A1 input
2A2	13	D2	12	I	Port 2 A2 input
2A3	15	C3	14	I	Port 2 A3 input
2A4	17	B2	16	I	Port 2 A4 input
2 OE	19	A4	18	I	Output enable
2Y1	9	E2	8	0	Port 2 Y1 output
2Y2	7	D3	6	0	Port 2 Y2 output
2Y3	5	C2	4	0	Port 2 Y3 output
2Y4	3	B3	2	0	Port 2 Y4 output
GND	10	E1	9	-	Ground
V <sub>cc</sub>	20	A3	19	-	Power pin



### **5** Specifications

### 5.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)<sup>(1)</sup>

			MIN	MAX	UNIT
V <sub>CC</sub>	Supply voltage		-0.5	6.5	V
VI	Input voltage <sup>(2)</sup>		-0.5	6.5	V
Vo	Voltage range applied to any output in the high	-impedance or power-off state <sup>(2)</sup>	-0.5	6.5	V
Vo	Voltage range applied to any output in the high	or low state <sup>(2) (3)</sup>	-0.5	V <sub>CC</sub> + 0.5	V
I <sub>IK</sub>	Input clamp current	V <sub>I</sub> < 0		-50	mA
I <sub>ОК</sub>	Output clamp current	V <sub>O</sub> < 0		-50	mA
I <sub>O</sub>	Continuous output current			±50	mA
	Continuous current through $V_{CC}$ or GND			±100	mA
P <sub>tot</sub>	Power dissipation	$T_A = -40^{\circ}C \text{ to } +125^{\circ}C^{(4)}$ (5)		500	mW
TJ	Junction temperature			150	°C
T <sub>stg</sub>	Storage temperature		-65	150	°C

(1) Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under Section 5.3 is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

(2) The input and output negative-voltage ratings may be exceeded if the input and output current ratings are observed.

(3) The value of  $V_{CC}$  is provided in the Section 5.3 table.

(4) For the DW package: above 70°C the value of P<sub>tot</sub> derates linearly with 8 mW/K.

(5) For the DB, DGV, N, NS, and PW packages: above 60°C the value of P<sub>tot</sub> derates linearly with 5.5 mW/K.

### 5.2 ESD Ratings

				VALUE	UNIT
V.		Electrostatic discharge	Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001 <sup>(1)</sup>	±2000	V
V(	ESD)	Electrostatic discharge	Charged-device model (CDM), per JEDEC specification JESD22-C101 <sup>(2)</sup>	±1000	v

(1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.

(2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

### **5.3 Recommended Operating Conditions**

over recommended o	perating free-air ter	nperature range	(unless otherwise noted) <sup>(1)</sup>
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			T <sub>A</sub> = 2	5°C	-40 TO	+85°C	–40 TO	+125°C	UNIT	
			MIN	MAX	MIN	MAX	MIN	MAX	UNIT	
	Supply voltage	Operating	1.65	3.6	1.65	3.6	1.65	3.6	V	
V <sub>CC</sub>	Supply voltage	Data retention only	1.5		1.5		1.5		v	
	High-level input voltage	V <sub>CC</sub> = 1.65 V to 1.95 V	0.65 × V <sub>CC</sub>		0.65 × V <sub>CC</sub>		0.65 × V <sub>CC</sub>			
V <sub>IH</sub>		$V_{CC}$ = 2.3 V to 2.7 V	1.7		1.7		1.7		V	
		$V_{CC}$ = 2.7 V to 3.6 V	2		2		2			
	Low-level input voltage	V <sub>CC</sub> = 1.65 V to 1.95 V		$0.35 \times V_{CC}$		$0.35 \times V_{CC}$		0.35 × V <sub>CC</sub>		
∕ <sub>IL</sub>		$V_{CC}$ = 2.3 V to 2.7 V		0.7		0.7		0.7	V	
		$V_{CC}$ = 2.7 V to 3.6 V		0.8		0.8		0.8		
V <sub>I</sub>	Input voltage		0	5.5	0	5.5	0	5.5	V	
Vo	Output voltage		0	V <sub>CC</sub>	0	V <sub>CC</sub>	0	V <sub>CC</sub>	V	
		V <sub>CC</sub> = 1.65 V		-4		-4		-4		
	High-level	V <sub>CC</sub> = 2.3 V		-8		-8		-8	mA	
ОН	output current	V <sub>CC</sub> = 2.7 V		–12		-12		-12	ША	
		V <sub>CC</sub> = 3 V		-24		-24		-24		
		V <sub>CC</sub> = 1.65 V		4		4		4		
	Low-level	V <sub>CC</sub> = 2.3 V		8		8		8	mA	
OL	output current	V <sub>CC</sub> = 2.7 V		12		12		12	ШA	
		V <sub>CC</sub> = 3 V		24		24		24		
Γ <sub>A</sub>	Ambient	BGA package			-40	85			°C	
A	temperature	All other packages					-40	125	C	

 All unused inputs of the device must be held at V<sub>CC</sub> or GND to ensure proper device operation. See *Implications of Slow or Floating* CMOS Inputs, SCBA004.

### **5.4 Thermal Information**

		SN74LVC244A										
	THERMAL METRIC <sup>(1)</sup>	DB <sup>(2)</sup> (SSOP)	DGV <sup>(2)</sup> (TVSOP)	DW <sup>(2)</sup> (SOIC)	ZQN <sup>(2)</sup> (BGA)	N <sup>(2)</sup> (PDIP)	NS <sup>(2)</sup> (SO)	PW <sup>(2)</sup> (TSSOP )	RGY <sup>(3)</sup> (VQFN)	RWP <sup>(3)</sup> (X1QFN)	RKS <sup>(3)</sup> (VQFN )	UNIT
						20 PIN	S					
R <sub>θJA</sub>	Junction-to-ambient thermal resistance	108.1	128.7	90.9	198.7	61.6	90.1	114.7	50.3	79.9	87.2	°C/W
R <sub>0JC(top)</sub>	Junction-to-case (top) thermal resistance	70.2	43.7	55.3	106.8	46.5	56.4	48.4	58.4	63.2	93.4	°C/W
R <sub>θJB</sub>	Junction-to-board thermal resistance	63.3	70.2	58.8	143.1	42.5	57.7	65.6	28.3	46.4	59.8	°C/W
Ψ <sub>JT</sub>	Junction-to-top characterization parameter	30.6	3.1	29.1	24.1	34.6	28.4	6.8	4.9	2.6	24.9	°C/W
Ψ <sub>JB</sub>	Junction-to-board characterization parameter	62.9	69.5	58.3	119.6	42.4	57.2	65.1	28.4	46.3	59.6	°C/W
R <sub>0JC(bot)</sub>	Junction-to-case (bottom) thermal resistance	_	_	_	n/a	_	_	_	22.7	27.3	44.3	°C/W

(1) For more information about traditional and new thermal metrics, see the Semiconductor and IC Package Thermal Metrics application report.

(2) The package thermal impedance is calculated in accordance with JESD 51-7.

(3) The package thermal impedance is calculated in accordance with JESD 51-5.



### **5.5 Electrical Characteristics**

over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS	V	T <sub>A</sub> = 25°C			–40 TO +85°C		–40 TO +125°C		UNIT	
PARAIVIETER	TEST CONDITIONS	V <sub>cc</sub>	MIN	TYP	MAX	MIN	MAX	MIN	MAX	UNIT	
	I <sub>OH</sub> = -100 μA	1.65 V to 3.6 V	V <sub>CC</sub> – 0.2			V <sub>CC</sub> - 0.2		V <sub>CC</sub> - 0.3			
	I <sub>OH</sub> = -4 mA	1.65 V	1.29			1.2		1.05			
V <sub>OH</sub>	I <sub>OH</sub> = -8 mA	2.3 V	1.9			1.7		1.55		V	
	L = 10 mA	2.7 V	2.2			2.2		2.05			
	I <sub>OH</sub> = -12 mA	3 V	2.4			2.4		2.25			
	I <sub>OH</sub> = -24 mA	3 V	2.3			2.2		2			
	I <sub>OL</sub> = 100 μA	1.65 V to 3.6 V			0.1		0.2		0.3	V	
V <sub>OL</sub>	I <sub>OL</sub> = 4 mA	1.65 V			0.24		0.45		0.6		
• OL	I <sub>OL</sub> = 8 mA	2.3 V			0.3		0.7		0.75		
	I <sub>OL</sub> = 12 mA	2.7 V			0.4		0.4		0.6		
	I <sub>OL</sub> = 24 mA	3 V			0.55		0.55		0.8		
l <sub>l</sub>	V <sub>I</sub> = 5.5 V or GND	3.6 V			±1		±5		±20	μA	
l <sub>off</sub>	V <sub>I</sub> or V <sub>O</sub> = 5.5 V	0			±1		±10		±20	μA	
I <sub>OZ</sub>	V <sub>O</sub> = 0 to 5.5 V	3.6 V			±1		±10		±20	μA	
1	$V_{I} = V_{CC}$ or GND	3.6 V			1		10		40		
Icc	$3.6 \text{ V} \le \text{V}_1 \le 5.5 \text{ V}^{(1)}$ $I_0 = 0$	3.0 V			1		10		40	μA	
ΔI <sub>CC</sub>	One input at $V_{CC}$ – 0.6 V, Other inputs at $V_{CC}$ or GND	2.7 V to 3.6 V			500		500		5000	μA	
C <sub>i</sub>	V <sub>I</sub> = V <sub>CC</sub> or GND	3.3 V		4						pF	
Co	V <sub>O</sub> = V <sub>CC</sub> or GND	3.3 V		5.5						pF	

(1) This applies in the disabled state only.

## 5.6 Switching Characteristics

DADAMETED	FROM	то	Vcc	TA	= 25°C		-40 TO +	85°C	-40 TO +125°	
PARAMETER	(INPUT)	(OUTPUT)		MIN	TYP	MAX	MIN	MAX	MIN MA	X
			1.5 V		7	14.4		14.9	16	.4
			1.8 V ± 0.15 V		5.9	10.4		10.9	12	.4
t <sub>pd</sub>	А	Y	2.5 V ± 0.2 V		4.2	7.4		7.9		0 ns
			2.7 V		4.2	6.7		6.9	8	.2
			3.3 V ± 0.3 V		3.9	5.7		5.9	7	.2
	$\overline{OE}  Y  \begin{array}{c ccccccccccccccccccccccccccccccccccc$	OE Y	1.5 V		8.3	17.8		18.3	19	.8
			1.8 V ± 0.15 V		6.4	12.1		12.6	14	.1
t <sub>en</sub>			2.5 V ± 0.2 V		4.6	9.1		9.6	11	.7 ns
t <sub>en</sub>			2.7 V		5	8.4		8.6	10	.3
			7.6	ç	.4					
			1.5 V		7.2	15.6		16.1	17	.6
			1.8 V ± 0.15 V		5.8	11.6		12.1	13	.6
t <sub>dis</sub>	ŌĒ	Y	2.5 V ± 0.2 V		3.7	7.3		7.8	ç	.9 ns
			2.7 V		3.8	6.6		6.8	8	.6
			3.3 V ± 0.3 V		3.8	6.3		6.5		8
t <sub>sk(o)</sub>			3.3 V ± 0.3 V					1	1	.5 ns

over recommended operating free-air temperature range (unless otherwise noted) (see Figure 6-1)

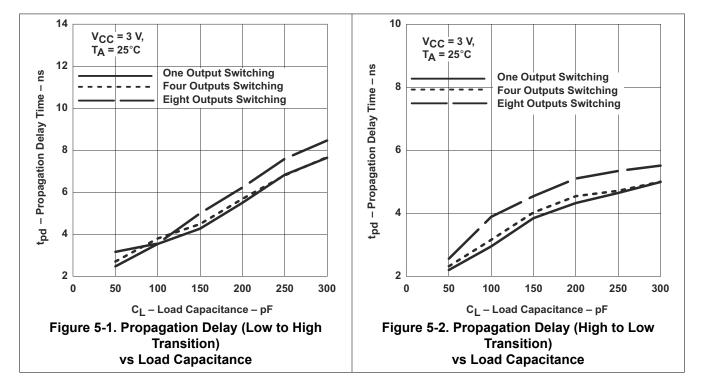
## **5.7 Operating Characteristics**

T<sub>A</sub> = 25°C

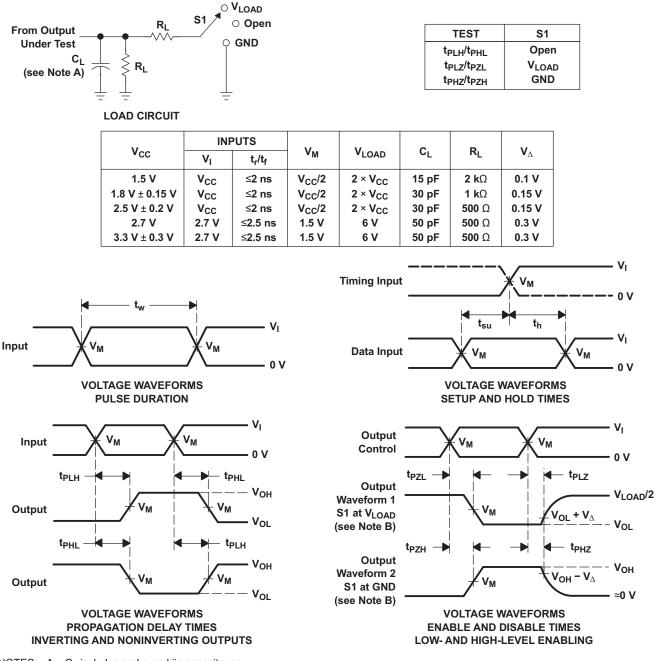
	PARAMETER	PARAMETER				UNIT
			1.8 V	43		
	Outputs enabled	f = 10 MHz	2.5 V	43		
	Dower dissinction consoltance per huffer/driver			3.3 V	44	<b>۳</b> ۲
C <sub>pd</sub>	Power dissipation capacitance per buffer/driver	Outputs disabled		1.8 V	1	pF
			f = 10 MHz	2.5 V	1	
				3.3 V		



### **5.8 Typical Characteristics**



### 6 Parameter Measurement Information



NOTES: A. C<sub>L</sub> includes probe and jig capacitance.

- B. Waveform 1 is for an output with internal conditions such that the output is low, except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high, except when disabled by the output control.
  C. All input pulses are supplied by generators having the following characteristics: PRR≤ 10 MHz, Z<sub>O</sub> = 50 Ω.
- D. The outputs are measured one at a time, with one transition per measurement.
- D. The outputs are measured one at a time, with one transition p
- E.  $t_{PLZ}$  and  $t_{PHZ}$  are the same as  $t_{dis}$ .
- F.  $t_{PZL}$  and  $t_{PZH}$  are the same as  $t_{en}$ .
- G.  $t_{PLH} \, \text{and} \, t_{PHL} \, \text{are the same as} \, t_{pd}.$
- H. All parameters and waveforms are not applicable to all devices.

#### Figure 6-1. Load Circuit and Voltage Waveforms



## 7 Detailed Description

### 7.1 Overview

The SN74LVC244A contains 8 individual high speed CMOS buffers organized as two 4-bit buffers/line drives with 3-state outputs.

Each buffer performs the boolean logic function xYn = xAn, with x being the bank number and n being the channel number.

Each output enable  $(x\overline{OE})$  controls four buffers. When the  $x\overline{OE}$  pin is in the low state, the outputs of all buffers in the bank x are enabled. When the  $x\overline{OE}$  pin is in the high state, the outputs of all buffers in the bank x are disabled. All disabled output are placed into the high-impedance state.

To put the device in the high-impedance state during power up or power down, tie both  $\overline{OE}$  pins to V<sub>CC</sub> through a pull-up resistor; the minimum value of the resistor is determined by the current sinking capability of the driver and the leakage of the pin as defined in the *Electrical Characteristics* table.

### 7.2 Functional Block Diagram

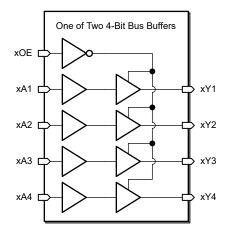


Figure 7-1. Logic Diagram (Positive Logic)

### 7.3 Feature Description

### 7.3.1 Balanced CMOS 3-State Outputs

This device includes balanced CMOS 3-state outputs. Driving high, driving low, and high impedance are the three states that these outputs can be in. The term *balanced* indicates that the device can sink and source similar currents. The drive capability of this device may create fast edges into light loads, so routing and load conditions should be considered to prevent ringing. Additionally, the outputs of this device can drive larger currents than the device can sustain without being damaged. It is important for the output power of the device to be limited to avoid damage due to overcurrent. The electrical and thermal limits defined in the *Absolute Maximum Ratings* must be followed at all times.

When placed into the high-impedance state, the output will neither source nor sink current, with the exception of minor leakage current as defined in the *Electrical Characteristics* table. In the high-impedance state, the output voltage is not controlled by the device and is dependent on external factors. If no other drivers are connected to the node, then this is known as a floating node and the voltage is unknown. A pull-up or pull-down resistor can be connected to the output to provide a known voltage at the output while it is in the high-impedance state. The value of the resistor will depend on multiple factors, including parasitic capacitance and power consumption limitations. Typically, a  $10k\Omega$  resistor can be used to meet these requirements.

Unused 3-state CMOS outputs should be left disconnected.



#### 7.3.2 Standard CMOS Inputs

This device includes standard CMOS inputs. Standard CMOS inputs are high impedance and are typically modeled as a resistor in parallel with the input capacitance given in the *Electrical Characteristics*. The worst case resistance is calculated with the maximum input voltage, given in the *Absolute Maximum Ratings*, and the maximum input leakage current, given in the *Electrical Characteristics*, using Ohm's law ( $R = V \div I$ ).

Standard CMOS inputs require that input signals transition between valid logic states quickly, as defined by the input transition time or rate in the *Recommended Operating Conditions* table. Failing to meet this specification will result in excessive power consumption and could cause oscillations. More details can be found in *Implications of Slow or Floating CMOS Inputs*.

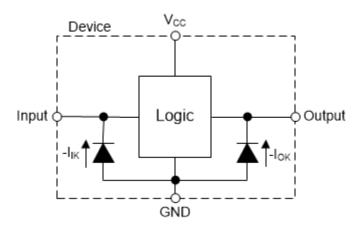
Do not leave standard CMOS inputs floating at any time during operation. Unused inputs must be terminated at  $V_{CC}$  or GND. If a system will not be actively driving an input at all times, then a pull-up or pull-down resistor can be added to provide a valid input voltage during these times. The resistor value will depend on multiple factors; a  $10k\Omega$  resistor, however, is recommended and will typically meet all requirements.

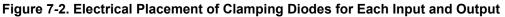
#### 7.3.3 Clamp Diode Structure

Figure 7-2 shows the inputs and outputs to this device have negative clamping diodes only.

#### CAUTION

Voltages beyond the values specified in the *Absolute Maximum Ratings* table can cause damage to the device. The input and output voltage ratings may be exceeded if the input and output clamp-current ratings are observed.





### 7.4 Device Functional Modes

Table 7-1 lists the functional modes of the SN74LVC244A.

INPU	OUTPUTS	
ŌĒ	Α	Y
L	L	L
L	Н	Н
Н	Х	Z

#### Table 7-1. Function Table

 (1) H = High Voltage Level, L = Low Voltage Level, X = Do Not Care, Z = High-Impedance State



### 8 Application and Implementation

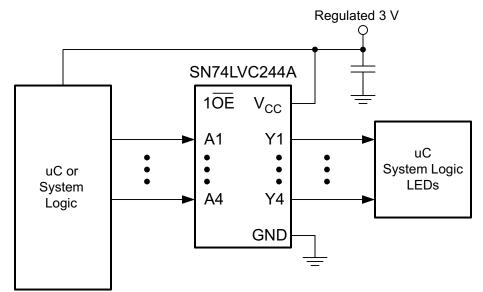
#### Note

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes, as well as validating and testing their design implementation to confirm system functionality.

### 8.1 Application Information

SN74LVC244A is a high drive CMOS device that can be used for a multitude of bus interface type applications where output drive or PCB trace length is a concern. The inputs can accept voltages to 5.5V at any valid  $V_{CC}$  making it ideal for down translation.

#### 8.2 Typical Application



**Figure 8-1. Application Schematic** 

#### 8.2.1 Design Requirements

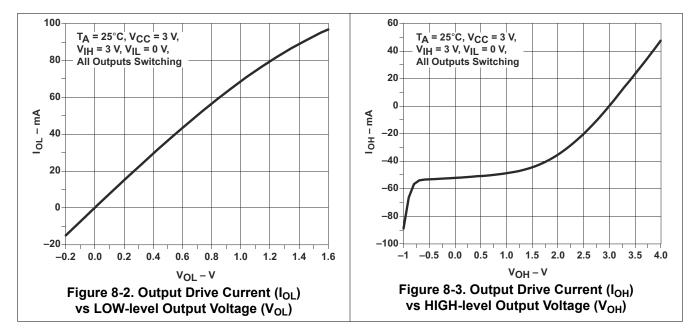
This device uses CMOS technology and has balanced output drive. Avoid bus contention because it can drive currents in excess of maximum limits. The high drive will also create fast edges into light loads, so consider routing and load conditions to prevent ringing.

#### 8.2.2 Detailed Design Procedure

- 1. Recommended Input Conditions:
  - For rise time and fall time specification, see ( $\Delta t/\Delta V$ ) in the Section 5.3 table.
  - For specified high and low levels, see ( $V_{IH}$  and  $V_{IL}$ ) in the Section 5.3 table.
  - Inputs are overvoltage tolerant allowing them to go as high as (V<sub>I</sub> max) in the Section 5.3 table at any valid  $V_{CC}$ .
- 2. Recommended maximum Output Conditions:
  - Load currents should not exceed (I<sub>O</sub> max) per output and should not exceed (Continuous current through V<sub>CC</sub> or GND) total current for the part. These limits are located in the Section 5.1 table.
  - Outputs should not be pulled above V<sub>CC</sub>.



### 8.2.3 Application Curves



### 8.3 Power Supply Recommendations

The power supply can be any voltage between the minimum and maximum supply voltage rating located in the *Recommended Operating Conditions*. Each  $V_{CC}$  terminal should have a good bypass capacitor to prevent power disturbance. A 0.1µF capacitor is recommended for this device. It is acceptable to parallel multiple bypass capacitors to reject different frequencies of noise. The 0.1µF and 1µF capacitors are commonly used in parallel. The bypass capacitor should be installed as close to the power terminal as possible for best results.

### 8.4 Layout

### 8.4.1 Layout Guidelines

- Bypass capacitor placement
  - Place near the positive supply terminal of the device
  - Provide an electrically short ground return path
  - Use wide traces to minimize impedance
  - Keep the device, capacitors, and traces on the same side of the board whenever possible
- Signal trace geometry
  - 8mil to 12mil trace width
  - Lengths less than 12cm to minimize transmission line effects
  - Avoid 90° corners for signal traces
  - Use an unbroken ground plane below signal traces
  - Flood fill areas around signal traces with ground
  - For traces longer than 12cm
    - Use impedance controlled traces
    - Source-terminate using a series damping resistor near the output
    - · Avoid branches; buffer signals that must branch separately



### 8.4.2 Layout Example

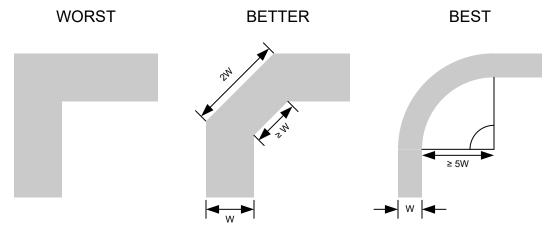
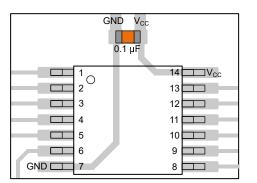
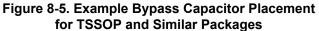


Figure 8-4. Example Trace Corners for Improved Signal Integrity





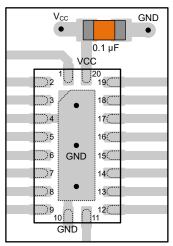


Figure 8-6. Example Bypass Capacitor Placement for WQFN and Similar Packages

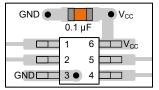


Figure 8-7. Example Bypass Capacitor Placement for SOT, SC70 and Similar Packages

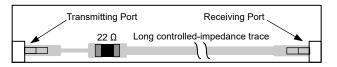


Figure 8-8. Example Damping Resistor Placement for Improved Signal Integrity



### 9 Device and Documentation Support

TI offers an extensive line of development tools. Tools and software to evaluate the performance of the device, generate code, and develop solutions are listed below.

#### 9.1 Documentation Support

#### 9.1.1 Related Documentation

For related documentation, see the following:

- Texas Instruments, CMOS Power Consumption and Cpd Calculation application report
- Texas Instruments, Designing With Logic application report
- Texas Instruments, *Thermal Characteristics of Standard Linear and Logic (SLL) Packages and Devices* application report

#### 9.2 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. Click on *Notifications* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

#### **9.3 Support Resources**

TI E2E<sup>™</sup> support forums are an engineer's go-to source for fast, verified answers and design help — straight from the experts. Search existing answers or ask your own question to get the quick design help you need.

Linked content is provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

#### 9.4 Trademarks

TI E2E<sup>™</sup> is a trademark of Texas Instruments.

All trademarks are the property of their respective owners.

### 9.5 Electrostatic Discharge Caution



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

### 9.6 Glossary

TI Glossary This glossary lists and explains terms, acronyms, and definitions.

### **10 Revision History**

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

С	hanges from Revision AC (October 2020) to Revision AD (March 2025)	Page
•	Added RKS (VQFN, 20) package option	1

Changes from Revision AB (November 2016) to Revision AC (October 2020)	Page
--	------



## 11 Mechanical, Packaging, and Orderable Information

The following pages include mechanical packaging and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser based versions of this data sheet, refer to the left hand navigation.



## PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
PSN74LVC244ARKSR	ACTIVE	VQFN	RKS	20	3000	TBD	Call TI	Call TI	-40 to 125		Samples
SN74LVC244ADBR	ACTIVE	SSOP	DB	20	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LC244A	Samples
SN74LVC244ADBRE4	ACTIVE	SSOP	DB	20	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LC244A	Samples
SN74LVC244ADBRG4	ACTIVE	SSOP	DB	20	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LC244A	Samples
SN74LVC244ADGVR	ACTIVE	TVSOP	DGV	20	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LC244A	Samples
SN74LVC244ADW	ACTIVE	SOIC	DW	20	25	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LVC244A	Samples
SN74LVC244ADWE4	ACTIVE	SOIC	DW	20	25	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LVC244A	Samples
SN74LVC244ADWG4	ACTIVE	SOIC	DW	20	25	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LVC244A	Samples
SN74LVC244ADWR	ACTIVE	SOIC	DW	20	2000	RoHS & Green	NIPDAU   SN	Level-1-260C-UNLIM	-40 to 125	LVC244A	Samples
SN74LVC244ADWRG4	ACTIVE	SOIC	DW	20	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LVC244A	Samples
SN74LVC244AN	ACTIVE	PDIP	N	20	20	RoHS & Green	NIPDAU	N / A for Pkg Type	-40 to 125	SN74LVC244AN	Samples
SN74LVC244ANSR	ACTIVE	SOP	NS	20	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LVC244A	Samples
SN74LVC244APW	ACTIVE	TSSOP	PW	20	70	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LC244A	Samples
SN74LVC244APWE4	ACTIVE	TSSOP	PW	20	70	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LC244A	Samples
SN74LVC244APWG4	ACTIVE	TSSOP	PW	20	70	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LC244A	Samples
SN74LVC244APWR	ACTIVE	TSSOP	PW	20	2000	RoHS & Green	NIPDAU   SN	Level-1-260C-UNLIM	-40 to 125	LC244A	Samples
SN74LVC244APWRE4	ACTIVE	TSSOP	PW	20	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LC244A	Samples
SN74LVC244APWRG3	ACTIVE	TSSOP	PW	20	2000	RoHS & Green	SN	Level-1-260C-UNLIM	-40 to 125	LC244A	Samples
SN74LVC244APWRG4	ACTIVE	TSSOP	PW	20	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LC244A	Samples
SN74LVC244APWT	ACTIVE	TSSOP	PW	20	250	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LC244A	Samples

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
SN74LVC244APWTE4	ACTIVE	TSSOP	PW	20	250	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LC244A	Samples
SN74LVC244APWTG4	ACTIVE	TSSOP	PW	20	250	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LC244A	Samples
SN74LVC244ARGYR	ACTIVE	VQFN	RGY	20	3000	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	LC244A	Samples
SN74LVC244ARGYRG4	ACTIVE	VQFN	RGY	20	3000	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	LC244A	Samples
SN74LVC244ARWPR	ACTIVE	X1QFN	RWP	20	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LC244A	Samples

<sup>(1)</sup> The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

**LIFEBUY:** TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

**PREVIEW:** Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

<sup>(2)</sup> RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

**RoHS Exempt:** TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

**Green:** TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

<sup>(3)</sup> MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

<sup>(4)</sup> There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

<sup>(5)</sup> Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

<sup>(6)</sup> Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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#### OTHER QUALIFIED VERSIONS OF SN74LVC244A :

• Automotive : SN74LVC244A-Q1

NOTE: Qualified Version Definitions:

• Automotive - Q100 devices qualified for high-reliability automotive applications targeting zero defects

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Texas

STRUMENTS

### TAPE AND REEL INFORMATION





#### QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal	I	<b>_</b> .			<u> </u>							
Device	Package Type	Package Drawing		SPQ	Reel Diameter		A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
					(mm)	W1 (mm)						
SN74LVC244ADBR	SSOP	DB	20	2000	330.0	16.4	8.2	7.5	2.5	12.0	16.0	Q1
SN74LVC244ADGVR	TVSOP	DGV	20	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1
SN74LVC244ADWR	SOIC	DW	20	2000	330.0	24.4	10.9	13.3	2.7	12.0	24.0	Q1
SN74LVC244ADWRG4	SOIC	DW	20	2000	330.0	24.4	10.8	13.3	2.7	12.0	24.0	Q1
SN74LVC244ANSR	SOP	NS	20	2000	330.0	24.4	8.4	13.0	2.5	12.0	24.0	Q1
SN74LVC244APWR	TSSOP	PW	20	2000	330.0	16.4	6.95	7.0	1.4	8.0	16.0	Q1
SN74LVC244APWRG3	TSSOP	PW	20	2000	330.0	16.4	6.95	7.1	1.6	8.0	16.0	Q1
SN74LVC244APWRG4	TSSOP	PW	20	2000	330.0	16.4	6.95	7.0	1.4	8.0	16.0	Q1
SN74LVC244APWT	TSSOP	PW	20	250	330.0	16.4	6.95	7.0	1.4	8.0	16.0	Q1
SN74LVC244ARGYR	VQFN	RGY	20	3000	330.0	12.4	3.8	4.8	1.6	8.0	12.0	Q1
SN74LVC244ARWPR	X1QFN	RWP	20	2000	178.0	13.5	2.85	3.65	0.75	8.0	12.0	Q1



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# PACKAGE MATERIALS INFORMATION

29-Jan-2025



Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
SN74LVC244ADBR	SSOP	DB	20	2000	356.0	356.0	35.0
SN74LVC244ADGVR	TVSOP	DGV	20	2000	356.0	356.0	35.0
SN74LVC244ADWR	SOIC	DW	20	2000	367.0	367.0	45.0
SN74LVC244ADWRG4	SOIC	DW	20	2000	367.0	367.0	45.0
SN74LVC244ANSR	SOP	NS	20	2000	367.0	367.0	45.0
SN74LVC244APWR	TSSOP	PW	20	2000	356.0	356.0	35.0
SN74LVC244APWRG3	TSSOP	PW	20	2000	364.0	364.0	27.0
SN74LVC244APWRG4	TSSOP	PW	20	2000	356.0	356.0	35.0
SN74LVC244APWT	TSSOP	PW	20	250	356.0	356.0	35.0
SN74LVC244ARGYR	VQFN	RGY	20	3000	356.0	356.0	35.0
SN74LVC244ARWPR	X1QFN	RWP	20	2000	189.0	185.0	36.0

## TEXAS INSTRUMENTS

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29-Jan-2025

## TUBE



## - B - Alignment groove width

#### \*All dimensions are nominal

Device	Package Name	Package Type	Pins	SPQ	L (mm)	W (mm)	Τ (μm)	B (mm)
SN74LVC244ADW	DW	SOIC	20	25	507	12.83	5080	6.6
SN74LVC244ADWE4	DW	SOIC	20	25	507	12.83	5080	6.6
SN74LVC244ADWG4	DW	SOIC	20	25	507	12.83	5080	6.6
SN74LVC244AN	N	PDIP	20	20	506	13.97	11230	4.32
SN74LVC244APW	PW	TSSOP	20	70	530	10.2	3600	3.5
SN74LVC244APWE4	PW	TSSOP	20	70	530	10.2	3600	3.5
SN74LVC244APWG4	PW	TSSOP	20	70	530	10.2	3600	3.5

# **PW0020A**



## **PACKAGE OUTLINE**

## TSSOP - 1.2 mm max height

SMALL OUTLINE PACKAGE



NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M. 2. This drawing is subject to change without notice. 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
- 5. Reference JEDEC registration MO-153.



## PW0020A

# **EXAMPLE BOARD LAYOUT**

## TSSOP - 1.2 mm max height

SMALL OUTLINE PACKAGE



NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



## PW0020A

# **EXAMPLE STENCIL DESIGN**

## TSSOP - 1.2 mm max height

SMALL OUTLINE PACKAGE



NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.



# **DB0020A**



# **PACKAGE OUTLINE**

SSOP - 2 mm max height

SMALL OUTLINE PACKAGE



NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M. 2. This drawing is subject to change without notice. 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
- 5. Reference JEDEC registration MO-150.



# DB0020A

# **EXAMPLE BOARD LAYOUT**

## SSOP - 2 mm max height

SMALL OUTLINE PACKAGE



NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



# DB0020A

# **EXAMPLE STENCIL DESIGN**

## SSOP - 2 mm max height

SMALL OUTLINE PACKAGE



NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.



# **RKS 20**

2.5 x 4.5, 0.5 mm pitch

# **GENERIC PACKAGE VIEW**

## VQFN - 1 mm max height

PLASTIC QUAD FLATPACK - NO LEAD

This image is a representation of the package family, actual package may vary. Refer to the product data sheet for package details.





## MECHANICAL DATA

### PLASTIC SMALL-OUTLINE PACKAGE

#### 0,51 0,35 ⊕0,25⊛ 1,27 8 14 0,15 NOM 5,60 8,20 5,00 7,40 $\bigcirc$ Gage Plane ₽ 0,25 7 1 1,05 0,55 0°-10° Δ 0,15 0,05 Seating Plane — 2,00 MAX 0,10PINS \*\* 14 16 20 24 DIM 10,50 10,50 12,90 15,30 A MAX A MIN 9,90 9,90 12,30 14,70 4040062/C 03/03

NOTES: A. All linear dimensions are in millimeters.

NS (R-PDSO-G\*\*)

**14-PINS SHOWN** 

- B. This drawing is subject to change without notice.
- C. Body dimensions do not include mold flash or protrusion, not to exceed 0,15.



## **GENERIC PACKAGE VIEW**

## VQFN - 1 mm max height

PLASTIC QUAD FGLATPACK - NO LEAD

3.5 x 4.5, 0.5 mm pitch

**RGY 20** 

This image is a representation of the package family, actual package may vary. Refer to the product data sheet for package details.





4225264/A

# **RGY0020A**



# **PACKAGE OUTLINE**

## VQFN - 1 mm max height

PLASTIC QUAD FLATPACK - NO LEAD



#### NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M. 2. This drawing is subject to change without notice.
- 3. The package thermal pad must be soldered to the printed circuit board for thermal and mechanical performance.



# **RGY0020A**

# **EXAMPLE BOARD LAYOUT**

## VQFN - 1 mm max height

PLASTIC QUAD FLATPACK - NO LEAD



NOTES: (continued)

4. This package is designed to be soldered to a thermal pad on the board. For more information, see Texas Instruments literature number SLUA271 (www.ti.com/lit/slua271).

5. Vias are optional depending on application, refer to device data sheet. If any vias are implemented, refer to their locations shown on this view. It is recommended that vias under paste be filled, plugged or tented.



# **RGY0020A**

# **EXAMPLE STENCIL DESIGN**

## VQFN - 1 mm max height

PLASTIC QUAD FLATPACK - NO LEAD



NOTES: (continued)

6. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.



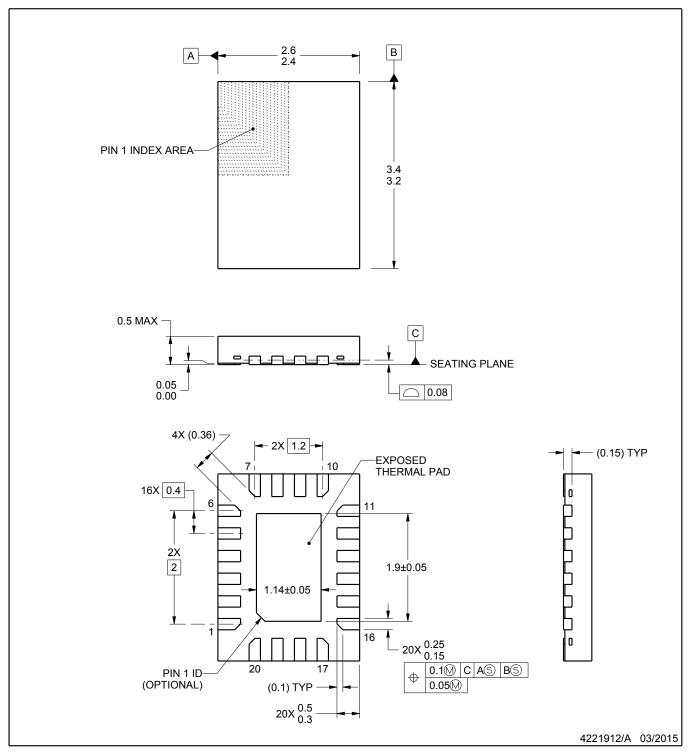
# **RWP0020A**



## **PACKAGE OUTLINE**

## X1QFN - 0.5 mm max height

PLASTIC QUAD FLATPACK - NO LEAD



#### NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M. 2. This drawing is subject to change without notice.
- 3. The package thermal pad must be soldered to the printed circuit board for thermal and mechanical performance.

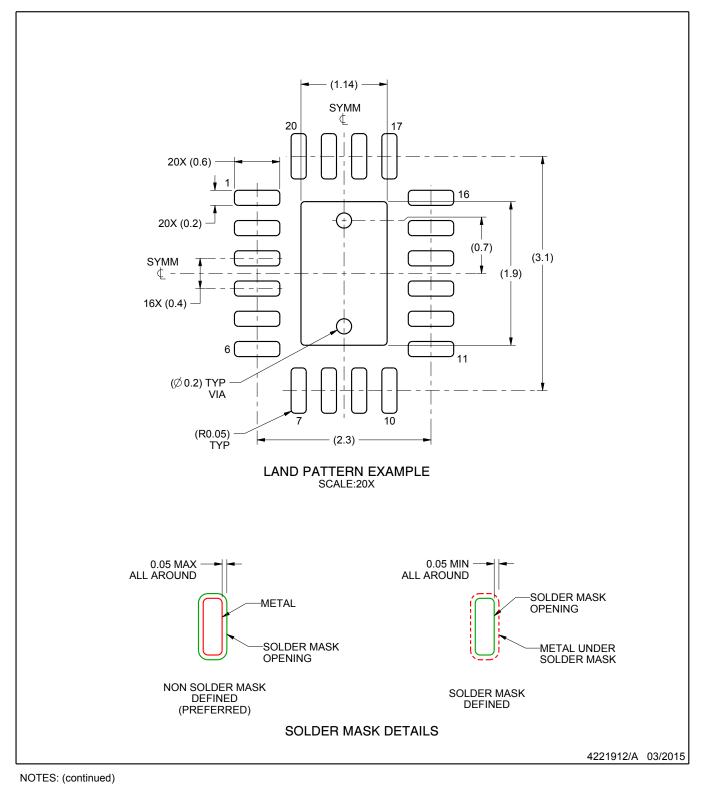


## **RWP0020A**

# **EXAMPLE BOARD LAYOUT**

## X1QFN - 0.5 mm max height

PLASTIC QUAD FLATPACK - NO LEAD



4. This package is designed to be soldered to a thermal pad on the board. For more information, see Texas Instruments literature number SLUA271 (www.ti.com/lit/slua271).

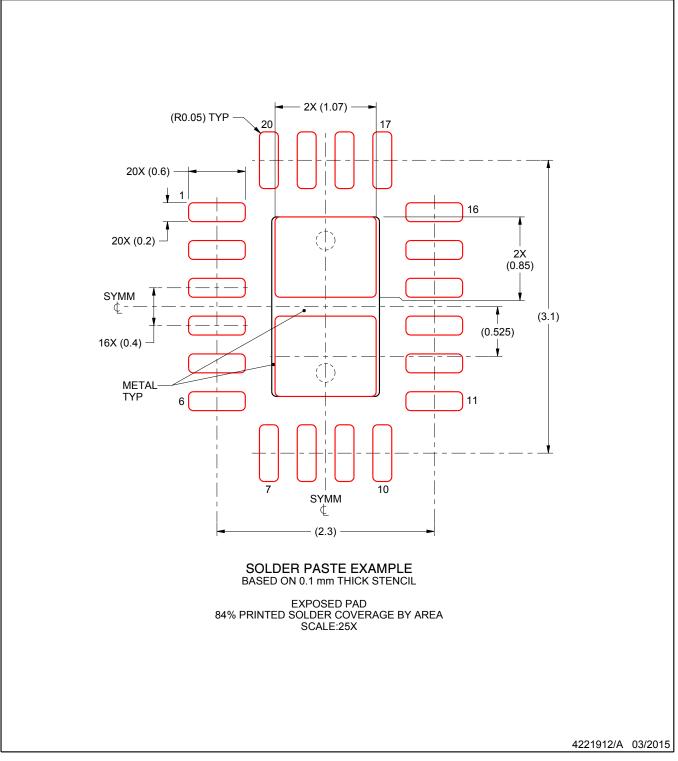


## **RWP0020A**

# **EXAMPLE STENCIL DESIGN**

## X1QFN - 0.5 mm max height

PLASTIC QUAD FLATPACK - NO LEAD



NOTES: (continued)

5. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.



## N (R-PDIP-T\*\*)

PLASTIC DUAL-IN-LINE PACKAGE

16 PINS SHOWN



NOTES:

- A. All linear dimensions are in inches (millimeters).B. This drawing is subject to change without notice.
- Falls within JEDEC MS-001, except 18 and 20 pin minimum body length (Dim A).
- $\triangle$  The 20 pin end lead shoulder width is a vendor option, either half or full width.



# **DW0020A**



## **PACKAGE OUTLINE**

## SOIC - 2.65 mm max height

SOIC



NOTES:

- 1. All linear dimensions are in millimeters. Dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M. 2. This drawing is subject to change without notice. 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.43 mm per side.
- 5. Reference JEDEC registration MS-013.



# DW0020A

# **EXAMPLE BOARD LAYOUT**

## SOIC - 2.65 mm max height

SOIC



NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



## DW0020A

# **EXAMPLE STENCIL DESIGN**

## SOIC - 2.65 mm max height

SOIC



NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.



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